Claims

1. A method of forming a substrate opening, comprising:

forming a plurality of side-by-side openings in a substrate, immediately adjacent of the side-by-side openings having a wall there between, at least some of the immediately adjacent side-by-side openings being formed in the substrate to different depths relative one another; and

removing all portions of said walls to form a larger opening having a non-vertical sidewall surface where the walls were removed in at least one straight-line vertical cross-section that passes through the non-vertical sidewall surface orthogonally to the removed walls, the larger opening being formed to have a straight non-horizontal base surface orthogonal to the at least one straight-line vertical cross-section, the substrate openings having the walls there-between that individually have multiple different maximum outermost open dimensions being individually trapezoidal in shape and the substrate openings which are individually trapezoidal in shape causing the larger opening to be formed to have a non-horizontal base surface extending along substantially all of the larger opening orthogonally to the at least one straight-line vertical cross-section.

2. A method of forming a substrate opening, comprising:

forming a plurality of side-by-side openings in a substrate, immediately adjacent of the side-by-side openings having a wall there-between, at least some of the immediately adjacent side-by-side openings being formed in the substrate to different depths relative one another;

removing all portions of said walls to form a larger opening having a non-vertical sidewall surface where the walls were removed in at least one straight-line vertical cross-section that passes through the non-vertical sidewall surface orthogonally to the removed walls;

the forming comprising etching and the removing comprising etching, the etching of the forming and the etching of the removing comprising a single continuous etching step from the forming through the removing; and

the continuous etching being at least one of (a) and (b), where

(a) using the same etching chemistry from beginning to end of the continuous etching; and

(b) plasma etching from beginning to end of the continuous etching.

3. The method of claim 2 comprising (a): using the same etching chemistry from beginning to end of the continuous etching.

4. The method of claim 2 comprising (b): plasma etching from beginning to end of the continuous etching.

5. The method of claim 4 wherein the continuous etching uses the same etching chemistry from beginning to end of the continuous etching.

6. The method of claim 4 wherein the continuous etching uses different etching chemistries between beginning and end of the continuous etching.

7. The method of claim 4 wherein the continuous etching uses the same etching conditions from beginning to end of the continuous etching.

8. The method of claim 4 wherein the continuous etching uses different etching conditions between beginning and end of the continuous etching.